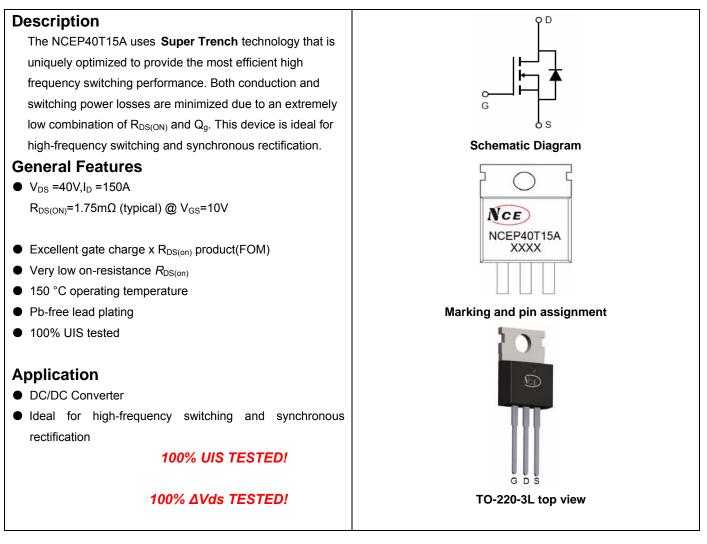


NCEP40T15A

NCE N-Channel Super Trench Power MOSFET



Package Marking and Ordering Information

Device Marking	Device	Device Package	Reel Size	Tape width	Quantity
NCEP40T15A	NCEP40T15A	TO-220-3L	-	-	-

Absolute Maximum Ratings (T_c=25℃unless otherwise noted)

Parameter	Symbol	Limit	Unit	
Drain-Source Voltage	Vds	40	V	
Gate-Source Voltage	Vgs	±20	V	
Drain Current-Continuous (Silicon Limited)	Ι _D	150	А	
Drain Current-Continuous(T _C =100°C)	I _D (100℃)	106	Α	
Pulsed Drain Current (Package Limited)	I _{DM}	400	A	
Maximum Power Dissipation	PD	210	W	
Derating factor		1.4	W/℃	
Single pulse avalanche energy (Note 5)	E _{AS}	720	mJ	
Operating Junction and Storage Temperature Range	TJ,TSTG	-55 To 175	°C	







Thermal Characteristic

Thermal Resistance, Junction-to-Case ^(Note 2)	R _{θJC}	0.71	°C /W
--	------------------	------	--------------

Electrical Characteristics (T_C=25[°]C unless otherwise noted)

Unit	Max	Тур	Min	Condition	Symbol	Parameter	
					· ·	Off Characteristics	
V	-		40	V _{GS} =0V I _D =250µA	BV _{DSS}	Drain-Source Breakdown Voltage	
μA	1	-	-	V _{DS} =40V,V _{GS} =0V	I _{DSS}	Zero Gate Voltage Drain Current	
nA	±100	-	-	V_{GS} =±20V, V_{DS} =0V	I _{GSS}	Gate-Body Leakage Current	
						On Characteristics (Note 3)	
V	3.4	2.7	2	V _{DS} =V _{GS} ,I _D =250µA	V _{GS(th)}	Gate Threshold Voltage	
mΩ	1.95	1.75	-	V_{GS} =10V, I _D =75A	R _{DS(ON)}	Drain-Source On-State Resistance	
S	-	80		V _{DS} =5V,I _D =75A	g fs	Forward Transconductance	
		I			- I - J	Dynamic Characteristics (Note4)	
PF	-	4900	-	N 00)()/ 0)/	Clss	Input Capacitance	
PF	-	1250	-	V_{DS} =20V, V_{GS} =0V,	C _{oss}	Output Capacitance	
PF	-	80	-	F=1.0MHz	C _{rss}	Reverse Transfer Capacitance	
						Switching Characteristics (Note 4)	
nS	-	12	-		t _{d(on)}	Turn-on Delay Time	
nS	-	6.5	-	V _{DD} =20V,I _D =75A	tr	Turn-on Rise Time	
nS	-	48	-	V_{GS} =10V, R_{G} =1.6 Ω	t _{d(off)}	Turn-Off Delay Time	
nS	-	8.0	-		t _f	Turn-Off Fall Time	
nC	-	81	-		Qg	Total Gate Charge	
nC		13	-	$V_{DS}=20V,I_{D}=75A,$	Q _{gs}	Gate-Source Charge	
nC		9	-	V _{GS} =10V	Q _{gd}	Gate-Drain Charge	
		. <u> </u>			· ·	Drain-Source Diode Characteristics	
V	1.2		-	V _{GS} =0V,I _S =75A	V _{SD}	Diode Forward Voltage (Note 3)	
Α	150	-	-		I _S	Diode Forward Current (Note 2)	
nS	29		-	T_J = 25°C, I_F = I_S	t _{rr}	Reverse Recovery Time	
nC	105		-	di/dt = 100A/µs ^(Note3)	Qrr	Reverse Recovery Charge	
	150 29	-	-	T _J = 25°C, I _F = I _S	I _S	Diode Forward Current ^(Note 2) Reverse Recovery Time	

Notes:

1. Repetitive Rating: Pulse width limited by maximum junction temperature.

2. Surface Mounted on FR4 Board, t ≤ 10 sec.

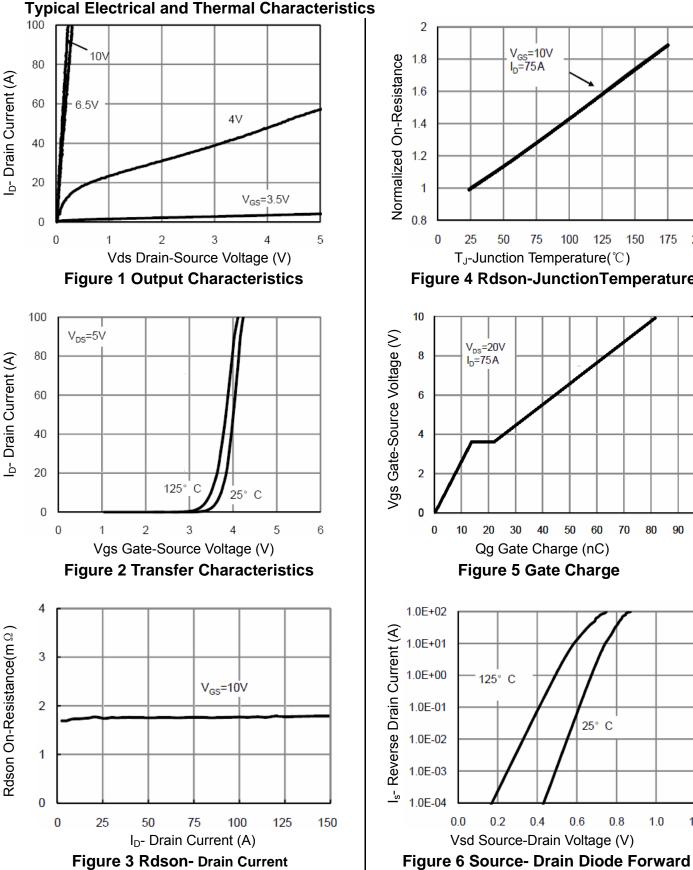
3. Pulse Test: Pulse Width ≤ 300µs, Duty Cycle ≤ 2%.

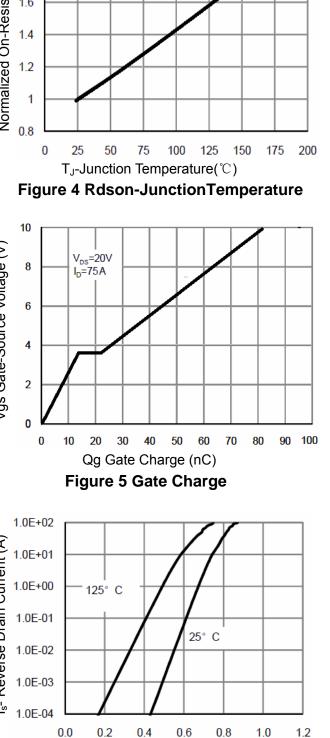
4. Guaranteed by design, not subject to production

5. EAS condition : Tj=25 $^\circ\!\mathrm{C}$,V_DD=20V,V_G=10V,L=0.5mH,Rg=25 Ω



http://www.ncepower.com





Pb Free Product

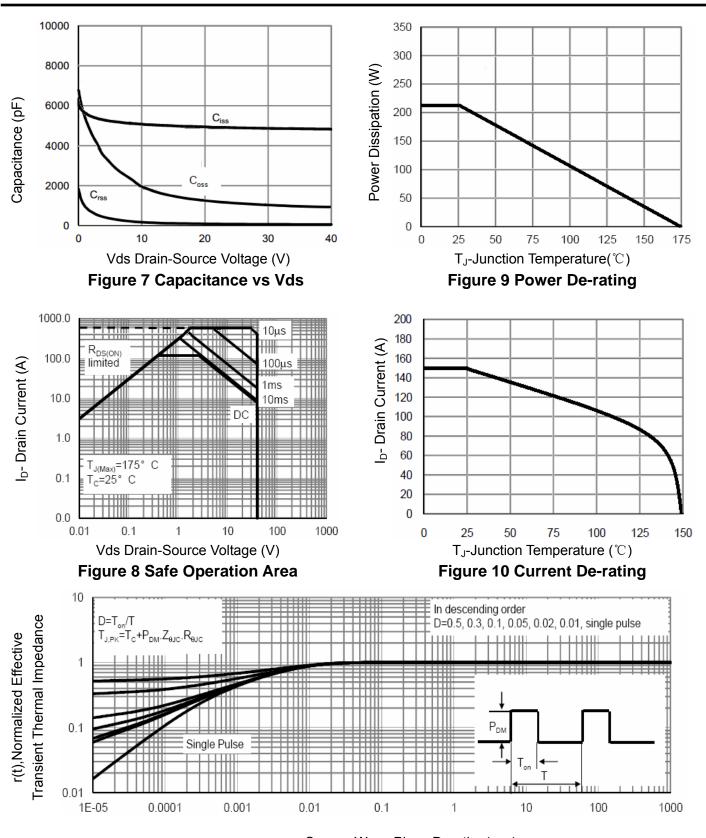
NCEP40T15A



http://www.ncepower.com



NCEP40T15A



Square Wave Pluse Duration(sec) Figure 11 Normalized Maximum Transient Thermal Impedance

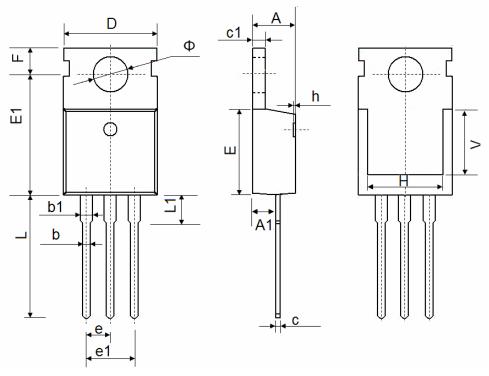


http://www.ncepower.com





TO-220-3L Package Information



Gumbal	Dimensions	In Millimeters	Dimensions In Inches		
Symbol	Min.	Max.	Min.	Max.	
А	4.400	4.600	0.173	0.181	
A1	2.250	2.550	0.089	0.100	
b	0.710	0.910	0.028	0.036	
b1	1.170	1.370	0.046	0.054	
С	0.330	0.650	0.013	0.026	
c1	1.200	1.400	0.047	0.055	
D	9.910	10.250	0.390	0.404	
E	8.9500	9.750	0.352	0.384	
E1	12.650	12.950	0.498	0.510	
е	2.540 TYP.		0.100 TYP.		
e1	4.980	5.180	0.196	0.204	
F	2.650	2.950	0.104	0.116	
Н	7.900	8.100	0.311	0.319	
h	0.000	0.300	0.000	0.012	
L	12.900	13.400	0.508	0.528	
L1	2.850	3.250	0.112	0.128	
V	7.500 REF.		0.295	REF.	
Ф	3.400	3.800	0.134	0.150	







Attention:

- Any and all NCE power products described or contained herein do not have specifications that can handle applications that require extremely high levels of reliability, such as life-support systems, aircraft's control systems, or other applications whose failure can be reasonably expected to result in serious physical and/or material damage. Consult with your NCE power representative nearest you before using any NCE power products described or contained herein in such applications.
- NCE power assumes no responsibility for equipment failures that result from using products at values that exceed, even momentarily, rated values (such as maximum ratings, operating condition ranges, or other parameters) listed in products specifications of any and all NCE power products described or contained herein.
- Specifications of any and all NCE power products described or contained herein stipulate the performance, characteristics, and functions of the described products in the independent state, and are not guarantees of the performance, characteristics, and functions of the described products as mounted in the customer's products or equipment. To verify symptoms and states that cannot be evaluated in an independent device, the customer should always evaluate and test devices mounted in the customer's products or equipment.
- NCE power Semiconductor CO.,LTD. strives to supply high-quality high-reliability products. However, any and all semiconductor products fail with some probability. It is possible that these probabilistic failures could give rise to accidents or events that could endanger human lives, that could give rise to smoke or fire, or that could cause damage to other property. When designing equipment, adopt safety measures so that these kinds of accidents or events cannot occur. Such measures include but are not limited to protective circuits and error prevention circuits for safe design, redundant design, and structural design.
- In the event that any or all NCE power products(including technical data, services) described or contained herein are controlled under any of applicable local export control laws and regulations, such products must not be exported without obtaining the export license from the authorities concerned in accordance with the above law.
- No part of this publication may be reproduced or transmitted in any form or by any means, electronic or mechanical, including photocopying and recording, or any information storage or retrieval system, or otherwise, without the prior written permission of NCE power Semiconductor CO.,LTD.
- Information (including circuit diagrams and circuit parameters) herein is for example only; it is not guaranteed for volume production. NCE power believes information herein is accurate and reliable, but no guarantees are made or implied regarding its use or any infringements of intellectual property rights or other rights of third parties.
- Any and all information described or contained herein are subject to change without notice due to product/technology improvement, etc. When designing equipment, refer to the "Delivery Specification" for the NCE power product that you intend to use.
- This catalog provides information as of Sep.2010. Specifications and information herein are subject to change without notice.